

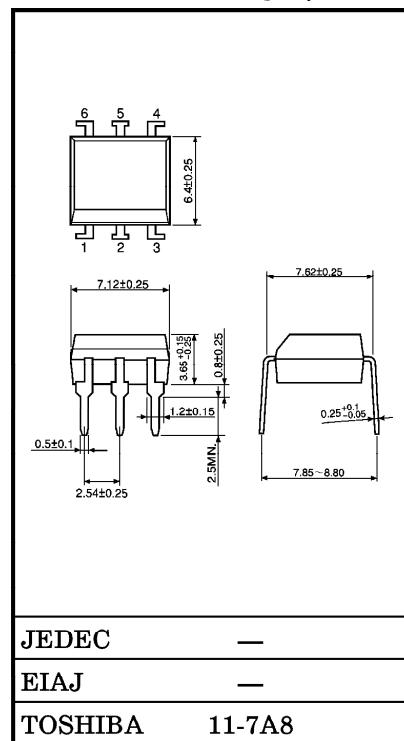
(4N25(Short))

AC LINE / DIGITAL LOGIC ISOLATOR.
 DIGITAL LOGIC / DIGITAL LOGIC ISOLATOR.
 TELEPHONE LINE RECEIVER.
 TWISTED PAIR LINE RECEIVER.
 HIGH FREQUENCY POWER SUPPLY FEEDBACK CONTROL.
 RELAY CONTACT MONITOR.

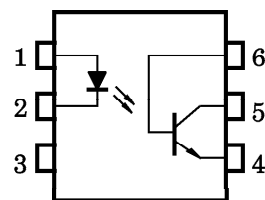
The TOSHIBA 4N25 (Short) through 4N28 (Short) consists of a gallium arsenide infrared emitting diode coupled with a silicon phototransistor in a dual in-line package.

- Switching Speeds : $3\mu s$ (Typ.)
- DC Current Transfer Ratio : 100% (Typ.)
- Isolation Resistance : $10^{11}\Omega$ (Min.)
- Isolation Voltage : 2500Vrms (Min.)
- UL Recognized : UL1577, File No. E67349

Unit in mm



PIN CONFIGURATIONS (TOP VIEW)



- 1 : ANODE
- 2 : CATHODE
- 3 : N.C.
- 4 : EMITTER
- 5 : COLLECTOR
- 6 : BASE

(4N25(Short))

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
LED	Forward Current (Continuous)	I _F	80	mA
	Forward Current Derating	ΔI _F / °C	1.07*	mA / °C
	Peak Forward Current (Note)	I _{PF}	3	A
	Power Dissipation	P _D	150	mW
	Power Dissipation Derating	ΔP _D / °C	2.0*	mW / °C
	Reverse Voltage	V _R	3	V
DETECTOR	Collector-Emitter Voltage	BV _{CEO}	30	V
	Collector-Base Voltage	BV _{CBO}	70	V
	Emitter-Collector Voltage	BV _{ECO}	7	V
	Collector Current (Continuous)	I _C	100	mA
	Power Dissipation	P _C	150	mW
	Power Dissipation Derating	ΔP _C / °C	2.0*	mW / °C
COUPLED	Storage Temperature Range	T _{stg}	−55~150	°C
	Operating Temperature Range	T _{opr}	−55~100	°C
	Lead Soldering Temperature (10s)	T _{sol}	260	°C
	Total Package Power Dissipation	P _T	250	mW
	Total Package Power Dissipation Derating	ΔP _T / °C	3.3*	mW / °C

Note : Pulse width 300μs, 2% duty cycle.

* Above 25°C ambient.

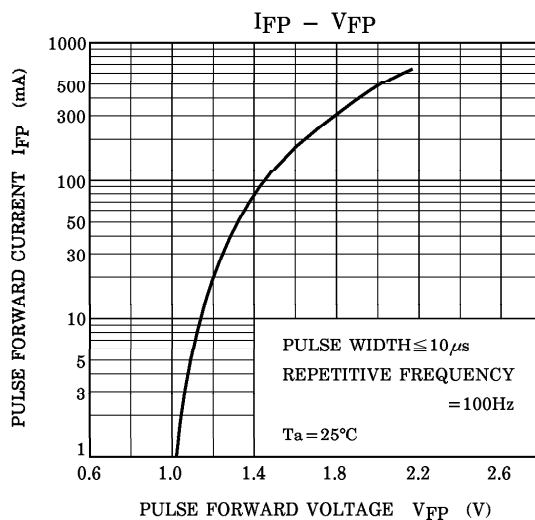
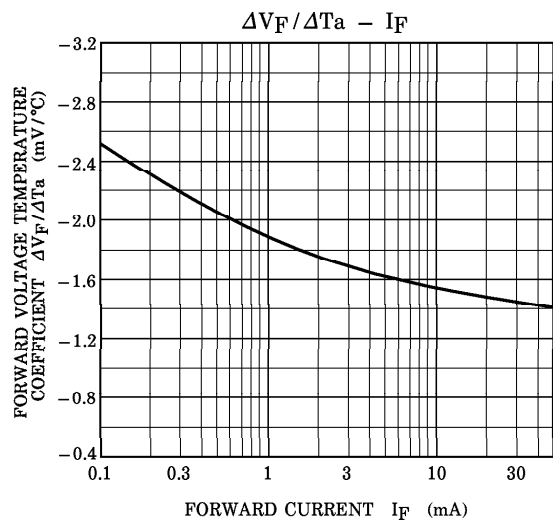
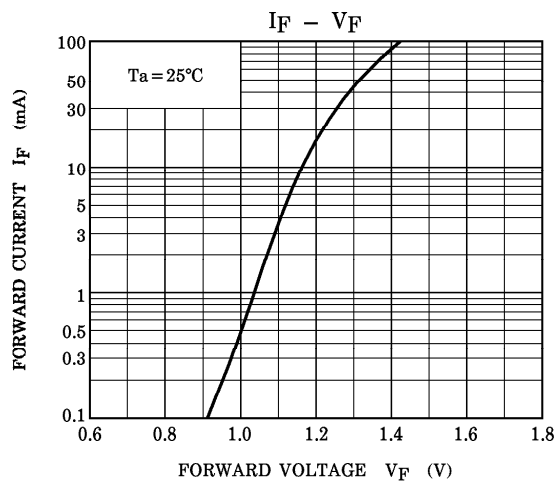
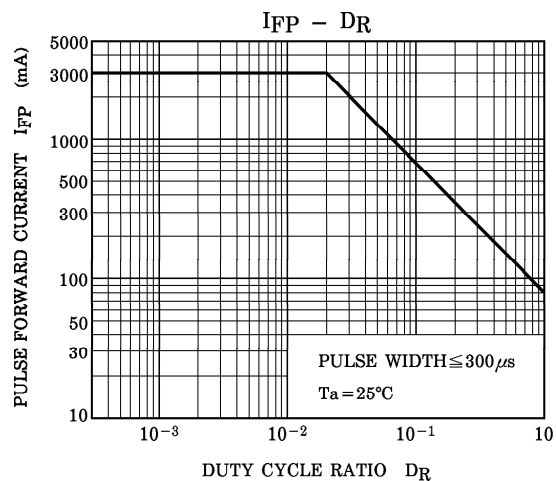
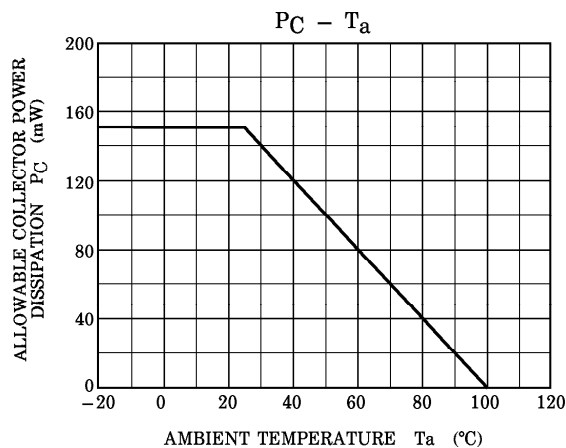
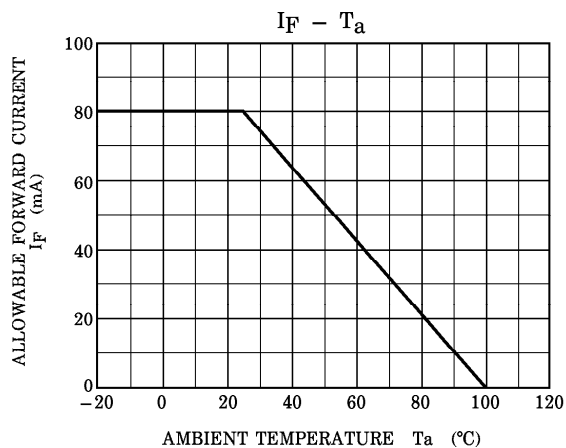
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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

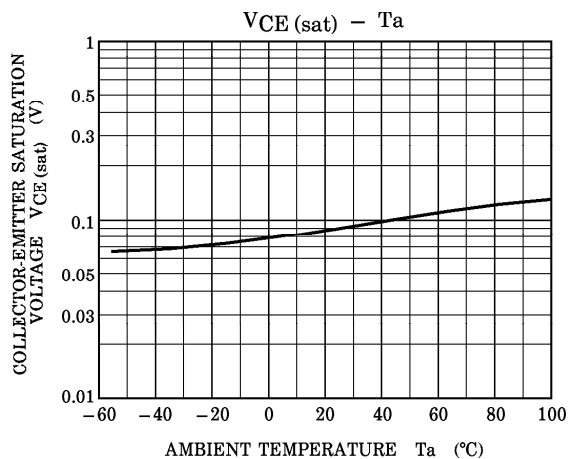
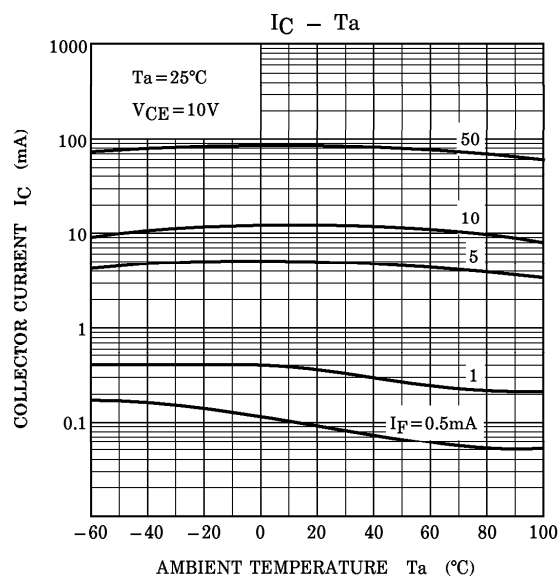
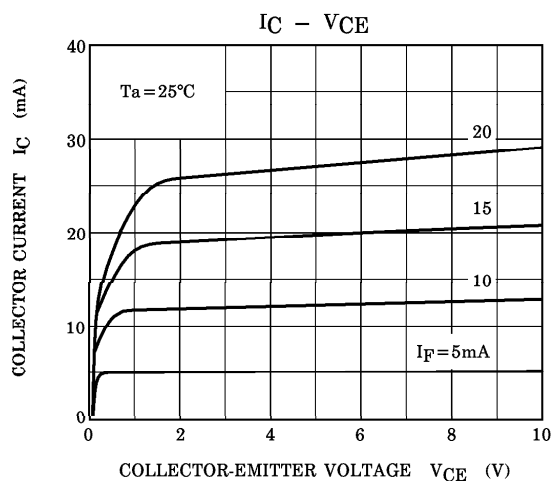
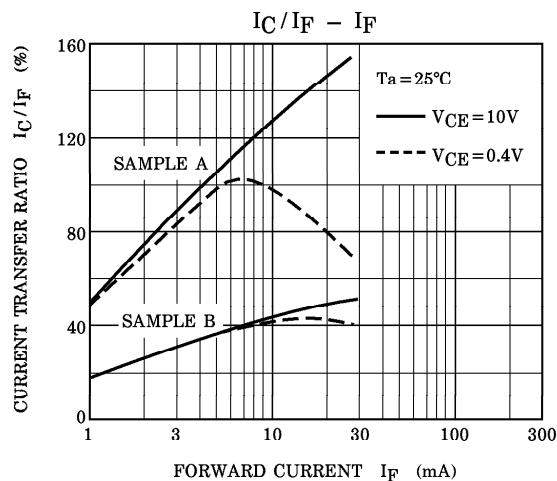
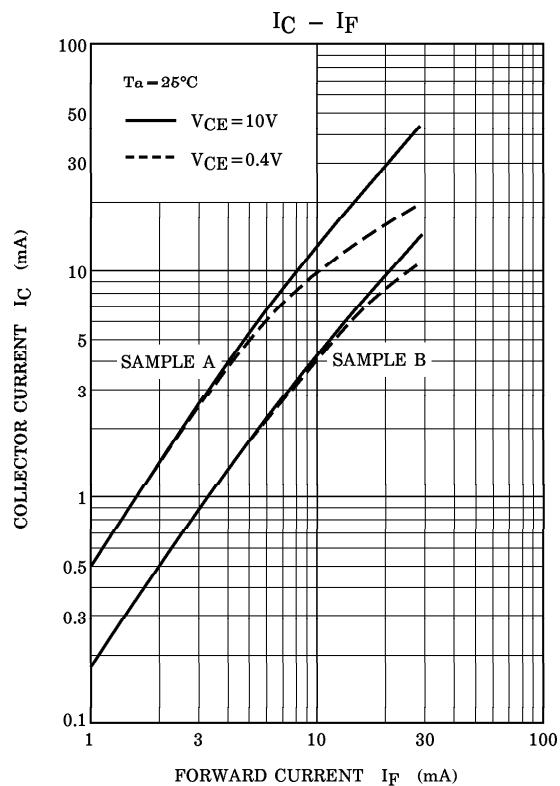
CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
LED	Forward Voltage	V _F	I _F = 10mA	—	1.15	1.5	V
	Reverse Current	I _R	V _R = 3V	—	—	100	μA
	Capacitance	C _D	V = 0, f = 1MHz	—	30	—	pF
DETECTOR	DC Forward Current Gain	h _{FE}	V _{CE} = 5V, I _C = 500μA	—	200	—	—
	Collector-Emitter Breakdown Voltage	V (BR) CEO	I _C = 1mA, I _F = 0	30	—	—	V
	Collector-Base Breakdown Voltage	V (BR) CBO	I _C = 100μA	70	—	—	V
	Emitter-Collector Breakdown Voltage	V (BR) ECO	I _E = 100μA	7	—	—	V
	Collector Dark Current	I _{CEO}	V _{CE} = 10V	—	1	50	nA
	Collector Dark Current	I _{CBO}	V _{CB} = 10V	—	0.1	20	nA
	Collector-Emitter Capacitance	C _{CE}	V = 0, f = 1MHz	—	10	—	pF
COUPLED	Current Transfer Ratio	I _C / I _F	I _F = 10mA, V _{CE} = 10V	20	100	—	%
	Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _F = 50mA, I _C = 2mA	—	0.1	0.5	V
	Capacitance Input to Output	C _S	V _S = 0, f = 1MHz	—	0.8	—	pF
	Isolation Resistance	R _S	V _S = 500V, R. H. ≤ 60%	10 ¹¹	—	—	Ω
	Isolation Voltage	BV _S	AC, 1 minute	2500	—	—	Vrms
		4N25, 4N25A	AC, Peak	2500	—	—	Vpk
		4N26, 4N27		1500	—	—	
		4N28		500	—	—	
		4N25A	AC, 1 second	1775	—	—	Vrms
	Rise / Fall Time	t _r / t _f	V _{CE} = 10V, I _C = 2mA R _L = 100Ω	—	2	—	μs
	Rise / Fall Time	t _r / t _f	V _{CB} = 10V, I _{CB} = 50μA R _L = 100Ω	—	200	—	ns

* JEDEC registered minimum BV_S, however, TOSHIBA specifies a minimum BV_S of 2500Vrms, 1 minute.

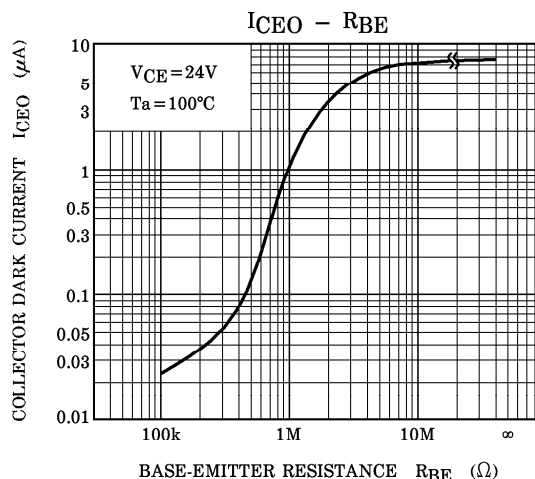
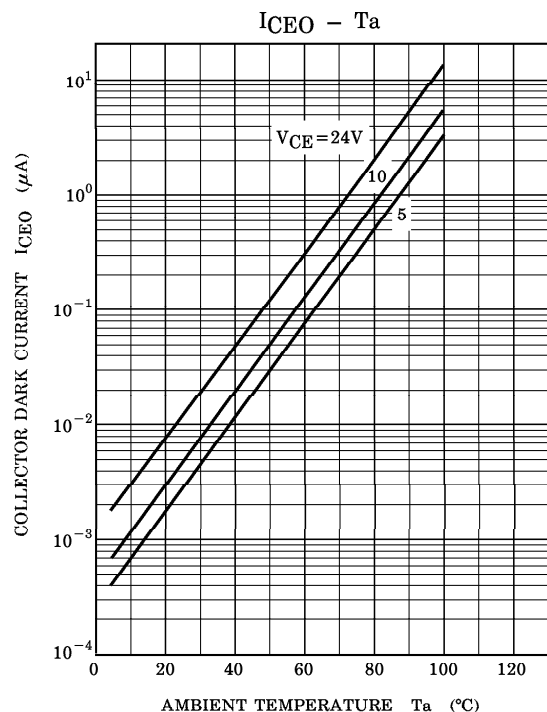
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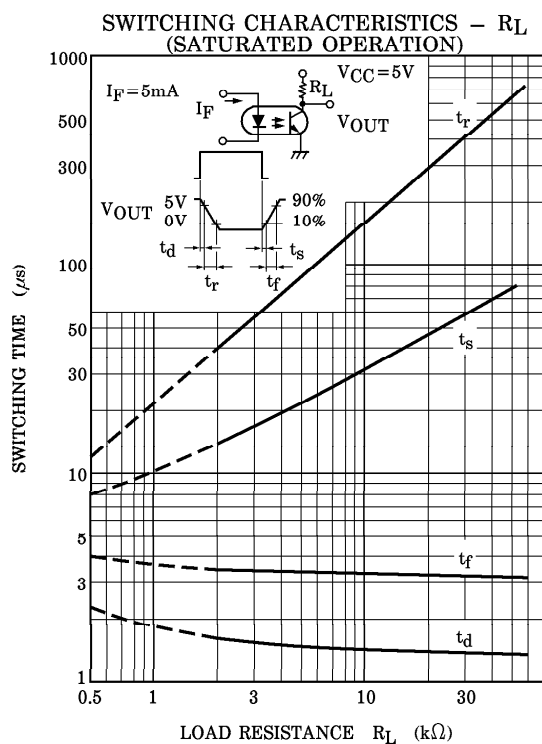
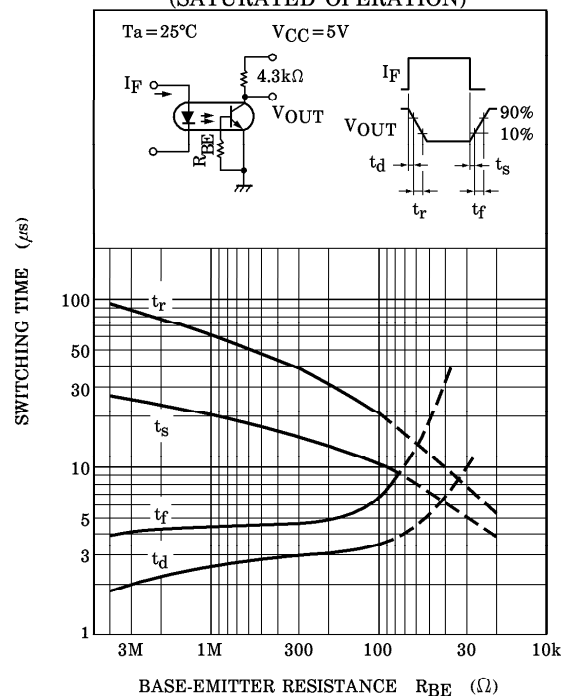
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SWITCHING CHARACTERISTICS - R_{BE}
(SATURATED OPERATION)



4N25(Short) - 6*

1996 - 4 - 8

TOSHIBA CORPORATION